



# 1.5 Gbps LVDS 4x4 CROSSPOINT SWITCH

## **FEATURES**

- Signaling Rates<sup>1</sup> >1.5 Gbps per Channel
- Supports Telecom/Datacom and HDTV Video Switching
- Non-Blocking Architecture Allows Each Output to be Connected to Any Input
- Total Jitter < 50ps</li>
- 330 mW When Operating at 1.5 Gbps
- Compatible With ANSI TIA/EIA-644-A LVDS Standard
- Available Packaging: 38-pin TSSOP
- 25 mV of Input Voltage Threshold Hysteresis
- Propagation Delay Times, 1 ns Maximum
- Inputs Electrically Compatible With LVPECL, CML and LVDS Signal Levels
- Inputs and Outputs High Impedance on Power Down
- Receiver Input and Driver Output ESD Exceeds 8 kV
- Operates From a Single 3.3-V Supply
- Integrated 110-Ω Line Termination Resistors Available With SN65LVDT125

## **APPLICATIONS**

• TBD

#### DESCRIPTION

The SN65LVDS125 and SN65LVDT125 are 4x4 nonblocking crosspoint switches. Low-voltage differential signaling (LVDS) is used to achieve signaling rates of 1.5 Gbps per channel. Each output driver includes a 4:1 multiplexer to allow any input to be routed to any output. Internal signal paths are fully differential to achieve the high signaling speeds while maintaining low signal skews. The SN65LVDT125 incorporates  $110\text{-}\Omega$  termination resistors for those applications where board space is a premium.

Designed to support signaling rates up to 1.5 Gbps for OC-12 clocks (622 MHz). The 1.5-Gbps signaling rate allows use in HDTV systems, including SMPTE 292 video applications requiring signaling rates of 1.485 Gbps. (Note: The ultimate rate and distance of data transfer is dependent upon the attenuation characteristics of the media, the noise coupling to the environment, and other application specific characteristics).

The SN65LVDS125 and SN65LVDT125 are characterized for operation from –40°C to 85°C.

#### SN65LVDS125DBT ( Marked as LVDS125) SN65LVDT125DBT ( Marked as LVDT125) (TOP VIEW)

S10	Ш	1 0	38	U vcc
S11	ш	2	37	□□ GND
1A		3	36	1Y
1B	ш	4	35	1Z
S20	ш	5	34	1DE
S21	ш	6	33	□□ 2Y
2A		7	32	2Z
2B	ш	8	31	□□ 2DE
GND	ш	9	30	□ GND
VCC		10	29	U vcc
GND		11	28	□ GND
ЗА		12	27	<b>□</b> □ 3Y
3B		13	26	□□ 3Z
S30		14	25	□□ 3DE
S31	ш	15	24	□□ 4Y
4A	ш	16	23	□□ 4Z
4B	ш	17	22	□□ 4DE
S40		18	21	□ GND
S41	ш	19	20	U vcc
				1

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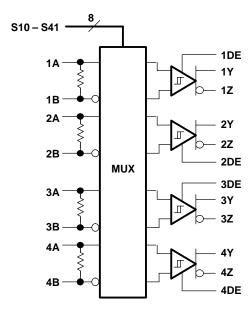
(1) The signaling rate of a line, is the number of voltage transitions that are made per second expressed in the units bps (bits per second).





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

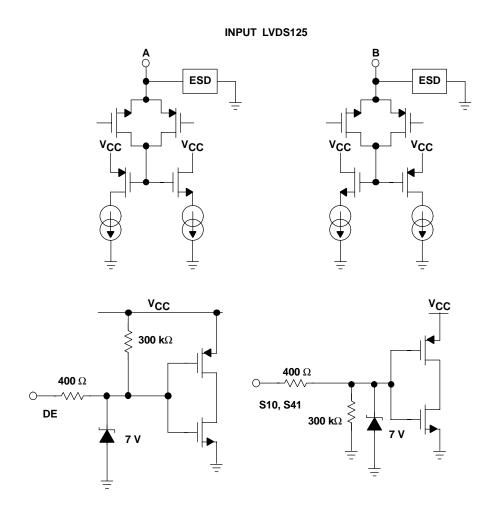
# **LOGIC DIAGRAM**



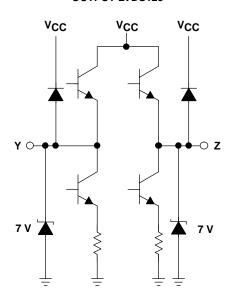
Integrated 110- Termination on LVDT Only



# **EQUIVALENT INPUT AND OUTPUT SCHEMATIC DIAGRAMS**



# **OUTPUT LVDS125**





# **CROSSPOINT LOGIC TABLES**

S10	S11	1Y/1Z	S20	S21	2Y/2Z	S30	S31	3Y/3Z	S40	S41	4Y/4Z
0	0	1A/1B									
0	1	2A/2B									
1	0	3A/3B									
1	1	4A/4B									

## PACKAGE DISSIPATION RATINGS

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C POWER}$ RATING	DERATING FACTOR <sup>(1)</sup> ABOVE $T_A = 25^{\circ}C$	T <sub>A</sub> = 85°C POWER RATING
DBT	1071 mW	8.5 mW/°C	556 mW

<sup>(1)</sup> This is the inverse of the junction-to-ambient thermal resistance when board-mounded and with no air flow.

# **ABSOLUTE MAXIMUM RATINGS**

over operating free-air temperature range unless otherwise noted(1)

			UNITS			
Supply voltage range, v <sub>CC</sub>	−0.5 V to 4 V					
	S, DE		-0.5 V to V <sub>CC</sub> + 2 V			
Maltananana	(A, B)		−0.7 V to 4 V			
Voltage range	VA - VB  (LVDT only)	V <sub>A</sub> – V <sub>B</sub>   (LVDT only)				
	(Y, Z)	(Y, Z)				
		A, B, Y, Z, and GND	±8 kV			
Elostrostatic discharge	Human body model <sup>(3)</sup>	All pins	±2 kV			
	Charged-device model <sup>(4)</sup>	Charged-device model <sup>(4)</sup> All pins				
Continuous power dissipation	Continuous power dissipation					
Storage temperature range	−65°C to 150°C					
Lead temperature 1,6 mm (1/1	260°C					

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

## RECOMMENDED OPERATING CONDITIONS

			MIN	NOM	MAX	UNIT
Supply voltage, V <sub>CC</sub>		3	3.3	3.6	V	
High-level input voltage, VIH	S10-S41, 1DE-4DE		2			V
Low-level input voltage, V <sub>IL</sub>	S10-S41, 1DE-4DE				0.8	V
	LVDS		0.05			V
Magnitude of differential input voltage  V <sub>ID</sub>	LVDT		0.05		0.8	V
Input voltage (any combination of common–mode or input signals)		0		3.3	V	
Operating free-air temperature, T <sub>A</sub>		-40		85	°C	

# TIMING SPECIFICATIONS

	PARAMETER			NOM	MAX	UNIT
tSET	Input to select setup time			0.5		ns
tHOLD	Input to select hold time	See Figure 6		0.5		ns
tSWITCH	Select to switch output			TBD	1.6	ns

<sup>(2)</sup> All voltage values, except differential I/O bus voltages, are with respect to network ground terminal.

<sup>(3)</sup> Tested in accordance with JEDEC Standard 22, Test Method A114-A.

<sup>(4)</sup> Tested in accordance with JEDEC Standard 22, Test Method C101.



# INPUT ELECTRICAL CHARACTERISTICS

over recommended operating conditions unless otherwise noted(1)

	PARAMETER		TEST CONDITIONS	MIN	TYP(1)	MAX	UNIT	
V <sub>IT+</sub>	Positive-going differential input voltage threshold		See Figure 1 and Table 1			50	mV	
V <sub>IT</sub> –	Negative-going differential input v threshold	oltage	See Figure 1 and Table 1	-50			mV	
VID(HYS)	Differential input voltage hysteres	is			25		mV	
l <sub>IH</sub>	High-level input current	1DE-4De S10-S41	V <sub>IH</sub> = 2 V			-10 20	μА	
IIL	Low-level input current	1DE-4DE S10-S41	V <sub>IL</sub> = 0.8 V			-10 20	μΑ	
	Input current (A or B inputs 'LVDS		V <sub>I</sub> = 0 V or 2.4 V, Second input at 1.2 V V <sub>I</sub> = 2.4 V or 3.3 V, Second input at 1.2 V	-20 0		20	μΑ	
lį			V <sub>CC</sub> = 1.5 V; V <sub>I</sub> = 0 V or 2.4V, Second input at 1.2 V	-40		40	μА	
	Input current (A or B inputs 'LVDT	7)	V <sub>CC</sub> = 1.5 V; V <sub>I</sub> = 2.4 V or 3.3 V, Second input at 1.2 V	0		66	μΑ	
	Input current (A or B inputs 11/DS	.,	V <sub>I</sub> = 0 V or 2.4 V, Other input open	-20 20		μΑ		
	Input current (A or B inputs 'LVDS)		V <sub>I</sub> = 2.4 V or 3.3 V, Other input open	0		33	μΑ	
I <sub>I</sub> (OFF)	Input ourset (A or D inputs 31)/D3		$V_{CC} = 1.5 \text{ V}; V_I = 0 \text{ V or } 2.4 \text{ V},$ Other input open	-40		40	μΑ	
	Input current (A or B inputs 'LVDT)		V <sub>CC</sub> = 1.5 V; V <sub>I</sub> = 2.4 V or 3.3 V, Other input open	0		66	μΑ	
IIO	Input offset current ( I <sub>IA</sub> - I <sub>IB</sub>  ) ('L	VDS)	$V_{IA} = V_{IB}$ , $0 \le V_{IA} \le 3.3 \text{ V}$	-6		6	μΑ	
VIT- thr VID(HYS) Diff IH High IIL Lo Inp III	Termination resistance ('LVDT)		$V_{ID} = 300 \text{ mV}, \ V_{IC} = 0 \text{ V to } 3.3 \text{ V}$	90	111	132	0	
KT	Termination resistance('LVDT with	n power-off)	$V_{ID} = 300 \text{ mV}, \ V_{IC} = 0 \text{ V to } 3.3 \text{ V}, \ V_{CC} = 1.5 \text{ V}$	90	111	132	7.2	
C-	Differential input capacitance('LVI	OT with	V <sub>I</sub> = 0.4 sin (4E6πt) + 0.5 V		3		132 Ω pF	
•	power-off)		Powered down		3		ρı	

<sup>(1)</sup> All typical values are at 25°C and with a 3.3 V supply.



## **OUTPUT ELECTRICAL CHARACTERISTICS**

over recommended operating conditions unless otherwise noted(1)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
IV <sub>OD</sub> I	Differential output voltage magnitude	See Figure 2	247	350	454	mV
△   V <sub>OD</sub>   Change in differential output voltage magnitude between logic states		$V_{ID} = \pm 100 \text{ mV}$	-50		50	mV
V <sub>OC</sub> (SS)	Steady-state common-mode output voltage		1.125		1.375	V
ΔVOC(SS)	Change in steady-state common-mode output voltage between logic states	See Figure 3	-50		50	mV
VOC(PP)	Peak-to-peak common-mode output voltage			50	150	mV
1	Complex assument	$R_L=100\Omega$ , $C_L=1$ pF		70	85	^
ICC	Supply current	Disabled		20	25	mA
los	Short-circuit output current	$V_{OY}$ or $V_{OZ} = 0$ V	-26		26	mA
IOSD	Differential short circuit output current	V <sub>OD</sub> = 0 V	-12		12	mA
loz	High-impedance output current	$V_O = 0 \text{ V or } V_{CC}$			±1	μΑ
СО	Differential output capacitance	$V_I = 0.4 \sin(4E6\pi t) + 0.5 V$		3		pF

# **SWITCHING CHARACTERISTICS**

over recommended operating conditions unless otherwise noted(1)

	. •					
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<sup>t</sup> PLH	Propagation delay time, low-to-high-level output		250		1000	
tPHL	Propagation delay time, high-to-low-level output	05	250		1000	
t <sub>r</sub>	Differential output signal rise time (20%–80%)	See Figure 4			220	ps
t <sub>f</sub>	Differential output signal fall time (20%–80%)				220	
tsk(p)	Pulse skew ( tpHL - tpLH )(1)			0	50	ps
tsk(o)	Channel-to-channel output skew(2)				50	ps
tsk(pp)	Part-to-part skew(3)				120	ps
<sup>t</sup> jit(per)	Period jitter, rms (1 standard deviation) <sup>(4)</sup>	750 MHz clock input <sup>(5)</sup>		1	3.7	ps
tjit(cc)	Cycle-to-cycle jitter (peak) <sup>(4)</sup>	750 MHz clock input <sup>(6)</sup>		6	23	ps
tjit(pp)	Peak-to-peak jitter <sup>(4)</sup>	1.5 Gbps 2 <sup>23</sup> –1 PRBS input <sup>(7)</sup>		28	65	ps
tjit(det)	Deterministic jitter, peak-to-peak <sup>(4)</sup>	1.5 Gbps 2 <sup>7</sup> –1 PRBS input <sup>(8)</sup>		17	48	ps
tPHZ	Propagation delay, high-level-to-high-impedance output				5	
tPLZ	Propagation delay, low-level-to-high-impedance output	Saa Firmura F			5	
<sup>t</sup> PZH	Propagation delay, high-impedance -to-high-level output	See Figure 5			20	ns
t <sub>PZL</sub>	Propagation delay, high-impedance-to-low-level output				20	

<sup>(1)</sup> t<sub>Sk(D)</sub> is the magnitude of the time difference between the tpLH and tpHL of any output of a single device.

<sup>(2)</sup>  $t_{sk(0)}$  is the maximum delay time difference between drivers over temperature, V<sub>CC</sub>, and process.

<sup>(3)</sup>  $t_{sk(pp)}$  is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

<sup>(4)</sup> Jitter is ensured by design and characterization. Stimulus jitter has been subtracted from the numbers.

<sup>(5)</sup> Input voltage =  $V_{1D}$  = 200 mV, 50% duty cycle at 750 MHz,  $t_r = t_f = 50$  ps (20% to 80%), measured over 1000 samples.

<sup>(6)</sup> Input voltage =  $V_{ID}$  = 200 mV, 50% duty cycle at 750 MHz,  $t_r$  =  $t_f$  = 50 ps (20% to 80%). (7) Input voltage =  $V_{ID}$  = 200 mV, 2<sup>23</sup>–1 PRBS pattern at 1.5 Gbps,  $t_r$  =  $t_f$  = 50 ps (20% to 80%), measured over 200k samples.

<sup>(8)</sup> Input voltage =  $V_{ID}$  = 200 mV, 2<sup>7</sup>–1 PRBS pattern at 1.5 Gbps,  $t_f = t_f = 50$  ps (20% to 80%).



## PARAMETER MEASUREMENT INFORMATION

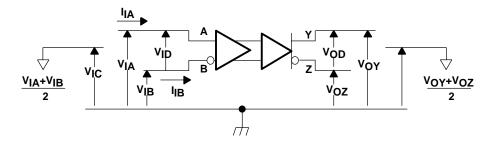


Figure 1. Voltage and Current Definitions

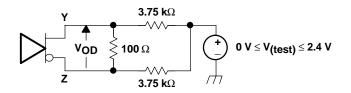
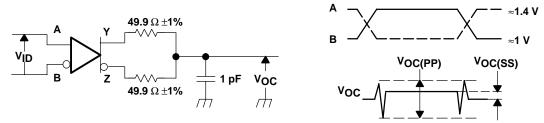
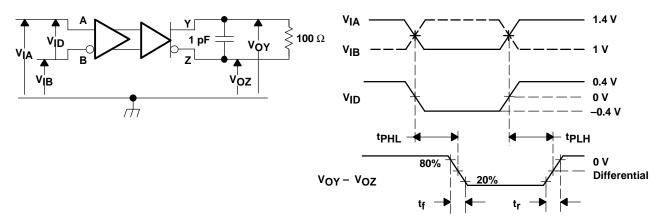


Figure 2. Differential Output Voltage (VOD) Test Circuit



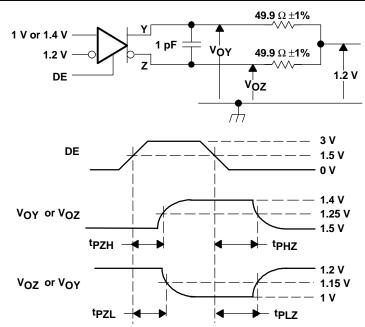
NOTE: All input pulses are supplied by a generator having the following characteristics: t<sub>r</sub> or t<sub>f</sub> ≤ 1 ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500 ±10 ns; R<sub>L</sub> = 100W; C<sub>L</sub> includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T.;the measurement of V<sub>OC</sub>(PP) is made on test equipment with a –3 dB bandwidth of at least 300 MHz.

Figure 3. Test Circuit and Definitions fot the Driver Common-Mode Output Voltage



NOTE: All input pulses are supplied by a generator having the following characteristics:  $t_f$  or  $t_f \le .25$  ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width = 500  $\pm$  10 ns .  $C_1$  includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T.

Figure 4. Timing Test Circuit and Waveforms

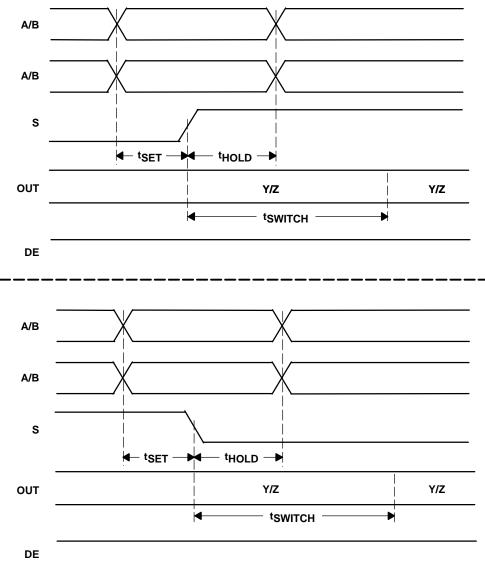


NOTE: A. All input pulses are supplied by a generator having the following characteristics:  $t_f$  or  $t_f \le 1$  ns, pulse-repetition rate (PRR) = 0.5 Mpps, pulse width =  $500 \pm 10$  ns .  $C_L$  includes instrumentation and fixture capacitance within 0,06 mm of the D.U.T.

Figure 5. Enable and Disable Time Circuit and Definitions

PRODUCT PREVIEW





NOTE: tSET and tHOLD times specify that data must be in a stable state before and after mux control switches.

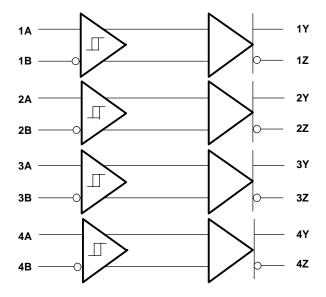
Figure 6. Input to Select for Both Rising and Falling Edge Setup and Hold Times

# PRODUCT PREVIEW

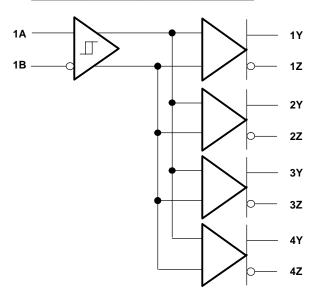
# **APPLICATION INFORMATION**

# **CONFIGURATION EXAMPLES**

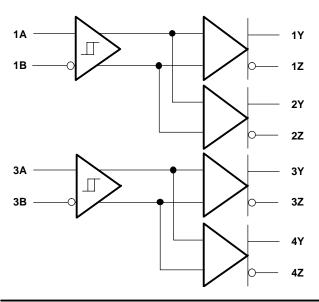
S10	S11	S20	S21
0	0	0 1	
S30	S31	S40	S41
1	0	1	1



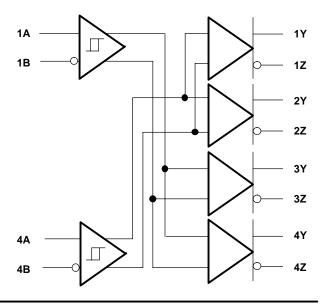
S10	S11	S20	S21
0	0	0	0
S30	S31	S40	S41
0	0	0	0



S10	S11	S20	S21
0	0	0	0
S30	S31	S40	S41
1	0	1	0

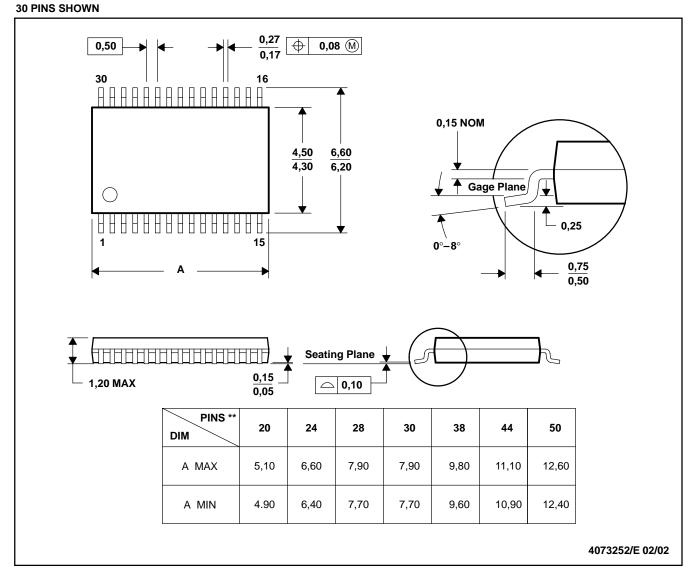


S10	S11	S20	S21
1	1	1	1
S30	S31	S40	S41
0	0	0	0



# DBT (R-PDSO-G\*\*)

# PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion.

D. Falls within JEDEC MO-153

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